

Title (en)

METHOD AND DEVICE FOR THE INTEGRATION OF SEMICONDUCTOR WAFERS

Title (de)

VERFAHREN UND VORRICHTUNG ZUR INTEGRATION VON HALBLEITER-WAFERN

Title (fr)

PROCÉDÉ ET DISPOSITIF POUR L'INTÉGRATION DE PASTILLES SEMI-CONDUCTRICES

Publication

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Application

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Abstract (en)

[origin: WO2019091728A1] The invention relates to a method for the integration of semiconductor components (9) in a confined space, in particular for 3D integration, in which, after positioning relative to a supporting substrate (10) and/or redistribution layer RDL (13) the semiconductor components (9) are protected and fixed in their relative position by introduction of a potting compound (12), is characterised in that before the introduction of the potting compound (12) a glass substrate (1) having a plurality of recesses (2) separated by partitions (3) to receive a semiconductor component (9) is positioned in such a way that the semiconductor component (9) is surrounded by the side wall surfaces (8) facing the semiconductor component of the respective partitions (3) of the glass substrate (1).

IPC 8 full level

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CPC (source: EP KR US)

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